





- Vcc regulator issues
 - Voltage follower design uses NFET (2N7002, BSS138, etc.).
 Vcc = Vref Vgs(off) and will vary widely with component tolerance and temperature. Does NOT provide precision regulation of Vcc.
 - REF pin performs like a low-current zener
 - Vref = 6.0uV +/- 0.3V @ 5uA and 25C
 - \blacksquare TC = -12mV/°C
 - \blacksquare Rz = 140k
 - Bias resistor and NFET must be chosen to insure Vcc remains in operational range over battery voltage and temperature extremes
 - Typical performance will have up to 0.5V drop in Vcc at 60C and 0.2V increase at 1C
 - Product testing at 25C should guard band test Vcc to 3.5V at minimum battery voltage to insure meeting 3.0V minimum Vcc at 60C.
 - Product testing at 25C should guard band test Vcc to 6.3V at maximum battery voltage (when charging) to insure meeting 6.5V maximum Vcc at 0C
 - Most designs should avoid external capacitor on REF pin



- Vcc regulator issues (cont'd)
 - Voltage regulator design uses N-channel JFET (SST113, etc.)
 Vcc is precision regulated by gauge and essentially independent of external component parameters
 - Vgs(off) must be less than Vcc at lowest possible current drain (sleep)
 - 0.001ufd cap on REG is recommended value
- Vout (EEPROM power) issues
 - Vout function only applies power to EEPROM when required
 - Reduced power drain during normal operation
 - No capacitor is recommended on Vout
 - Capacitor will rob charge from Vcc when Vout is switched on and could cause unintended device reset when Vout is powered
 - Current draw of EEPROM may pull Vcc back into POR during power up of gauge. Immediate loss of Vout to EEPROM forces reset of EEPROM communications



- RBI issues
 - Must have series diode from first cell tap of Lithium battery
 - If cell voltage is less than Vcc, then charging current could flow into first cell if diode were not present
 - Not required if battery is only single cell battery
 - Must have series resistor (10Meg) in series with first cell tap
 - If cell voltage is greater than Vcc, the IC could draw all Vcc current from cell tap and unbalance the battery
 - Vcc and RBI are connected by FET that is on if Vcc > POR threshold
 - If Vcc drops, current through 10Meg will force voltage at RBI pin to drop below POR and disconnect all internal load except RAM
 - If unused, tie RBI to Vcc
 - Cap only on RBI is useful to support RAM power through short transients
 - Must have some means to determine whether RAM power is lost and RAM data has been corrupted



RBI issues

- RBI function comparison
 - bq2050, bq2013h, bq2014h, bq2050h, bq2052, bq2913
 - Firmware does RAM corruption check after reset and does not reload original LMD and clear NAC if no corruption is detected
 - **Bq2060**
 - Firmware does RAM corruption check after reset and does not reload any RAM from EEPROM if no corruption is detected
 - bq2060A anc bq2063
 - Firmware does RAM corruption check after reset and does not set: RemainingCapacity=0, MaxError=100%, or Relearn_Flag=1 if no corruption is detected. All other RAM is reloaded from EEPROM
 - Battery Monitors (bq2018, bq2023, and bq26220)
 - All RAM is maintained by RBI. There is no hardware check for corruption. Data integrity determination is host responsibility
 - bq2018 -- all memory backed up
 - bq2023 -- all counters and 1 page of memory backed up
 - bq26220 -- all counters backed up, RAM is refreshed from flash on POR



- Sense resistor location
 - Normal location is between Vss of gauge and Bat-
 - Best location to maintain highest communication signal-to-noise ratio
 - Required location for single-ended VFC measurements (except bq2011)
 - Accuracy of gauges like bq2010 series and bq2040 too poor for voltage drop of sense resistor to be large issue
 - bq2060 measures Vsr and corrects battery voltage reading for Vsr drop
 - bq29311 AFE does not include Vsr in cell measurements sent to bq2083
 - Alternate location is between Vss of gauge and Pack-
 - bq2011 does this to allow larger voltage drop across sense resistor during discharge without issue of forward biasing ESD protection diode on SR pin
 - Can't use DQ communication if large signal allowed
 - bq2063 Vss must tie to Seiko S-8243 Vss
 - Cannot have Vcc modulated by Vsr
 - S-8243 makes lowest cell voltage measurement with respect to Vss
 - bq26200 uses single-ended voltage measurement
 - Differential VFC input allows flexible Rsr location
 - Low Vsr drop insufficient to cause HDQ communication issue



- VFC inputs
 - Recommended 100k and 0.1ufd filter on each input
 - Low-pass filtering reduces high-frequency noise and does not change the average value of the integrated waveform
 - High impedance reduces risk of damage to the SR inputs from ESD or momentary shorts of the battery
 - Place SR bypass caps as close as possible to the gauge, with short leads to both SR inputs and Vss
 - Tie VFC input sense leads to inside of sense resistor at point where etch is not carrying high current
 - "Kelvin" type connection
 - Adds least etch resistance in series with the sense resistor
- Coulomb counter inputs (bq2083)
 - Recommended 100 ohms and shunt 0.1ufd cap on each input plus 0.1ufd differential cap
 - Place the 3 caps as close to SR input pins as possible
 - Optimal layout can achieve 1uV offset difference to calibrated offset measured internally to IC.
 - Data flash board offset value allows setting external offset correction

Page 7



- Sense resistor temperature coefficient
 - Not much concern with lower accuracy gauges
 - Noticeable current drift after high current application if poor temperature coefficient used
 - Especially evident with high accuracy of bq2063 and bq2083 current reporting
 - Recommendation is +/-75ppm/°C
- Keep high-current and low-current grounds separate
 - ESD improvement
 - Measurement accuracy improvement
 - Lower VFC offset
 - Tie grounds together at same point as sense lead connection to sense resistor.
 - Vss connection is reference for single-ended VFC measurements as well as single-ended current measurement by the bq2060 and bq2063.